

Application No.: 09/934,864

Docket No.: END920000183US1  
(20135/00331)**LISTING OF THE CLAIMS**

The listing of claims will replace all prior versions, and listings, of claims in the application.

Please cancel claims 12-14 without prejudice to their reentry at some later date.

1. (Currently Amended) A method for recovering an organic solvent from a waste stream comprising supercritical CO<sub>2</sub>, an organic solvent and etching contaminants which comprises:

a) separating the supercritical CO<sub>2</sub> by subjecting the waste stream to elevated temperature or reduced pressure or both, to thereby obtain a first composition containing the supercritical CO<sub>2</sub> and a second stream composition containing the organic solvent and being at least substantially free of the supercritical CO<sub>2</sub>, and then

b) removing non-volatile etching contaminants from the second stream composition to recover the organic solvent free of the etching contaminants  
and wherein said temperature is about 20°C to about 150°C and said pressure is about 15 to about 750 torr.

2. (Original) The method of claim 1 which comprises removing the non-volatile etching contaminants via evaporation

3. (Original) The method of claim 1 which comprises removing the non-volatile etching contaminants by distillation.

4. (Original) The method of claim 1 which comprises removing the non-volatile etching contaminants by filtration.

5. (Original) The method of claim 1 which comprises removing the non-volatile etching contaminants by centrifugation.

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6. (Original) The method of claim 1 which comprises removing the non-volatile etching contaminants by settling.
7. (Original) The method of claim 1 wherein the organic solvent is selected from the group consisting of propylene carbonate, homologs thereof, N-methyl pyrrolidone and gamma butyrolactone.
8. (Original) The method of claim 1 wherein the organic solvent comprises propylene carbonate or homolog thereof.
9. (Original) The method of claim 1 wherein the organic solvent comprises propylene carbonates.
10. (Original) The method of claim 3 wherein the distillation comprises fractional distillation.
11. (Currently Amended) The method of claim 3 2 wherein the ~~distillation~~ evaporation comprises sequential evaporations.
- 12-14 (Canceled)
15. (Original) The method of claim 1 wherein the waste stream contains about 0.1 to about 3 molar of the supercritical CO<sub>2</sub>.
16. (Original) The method of claim 1 wherein the etching contaminants comprises at least one member selected from the group consisting of silicon nitride, silicon dioxide, and ammonium fluoride
17. (Currently Amended) A method for recovering propylene carbonate from a waste stream comprising supercritical CO<sub>2</sub>, propylene carbonate and etching contaminants which comprises:

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a) separating the supercritical CO<sub>2</sub> by subjecting the waste stream to elevated temperature or reduced pressure or both, to thereby obtain a first composition containing the supercritical CO<sub>2</sub> and a second stream composition containing propylene carbonate and being at least substantially free of the supercritical CO<sub>2</sub>, and then

b) removing non-volatile etching contaminants from the second stream composition by at least one process selected from the group consisting of evaporation, distillation, filtration, centrifugation and settling to recover the said settling of the etching contaminants to recover the organic solvent free of the etching contaminants

and wherein said temperature is about 20°C to about 150°C and said pressure is about ~~46~~ 15 to about 75 torr.

18. (Original) The method of claim 17 wherein the waste stream contains about 0.1 to about 3 molar of the supercritical CO<sub>2</sub>.

19. (Original) The method of claim 18 wherein the etching contaminants comprises at least one member selected from the group consisting of silicon nitride, silicon dioxide, and ammonium fluoride.

20. (Original) The method of claim 17 wherein the etching contaminants comprises at least one member selected from the group consisting of silicon nitride, silicon dioxide, and ammonium fluoride.

21. (New) The method of claim 17 which comprises removing the non-volatile etching contaminants via evaporation.

22. (New) The method of claim 17 which comprises removing the non-volatile etching contaminants by distillation.

23. (New) The method of claim 17 which comprises removing the non-volatile etching contaminants by centrifugation.